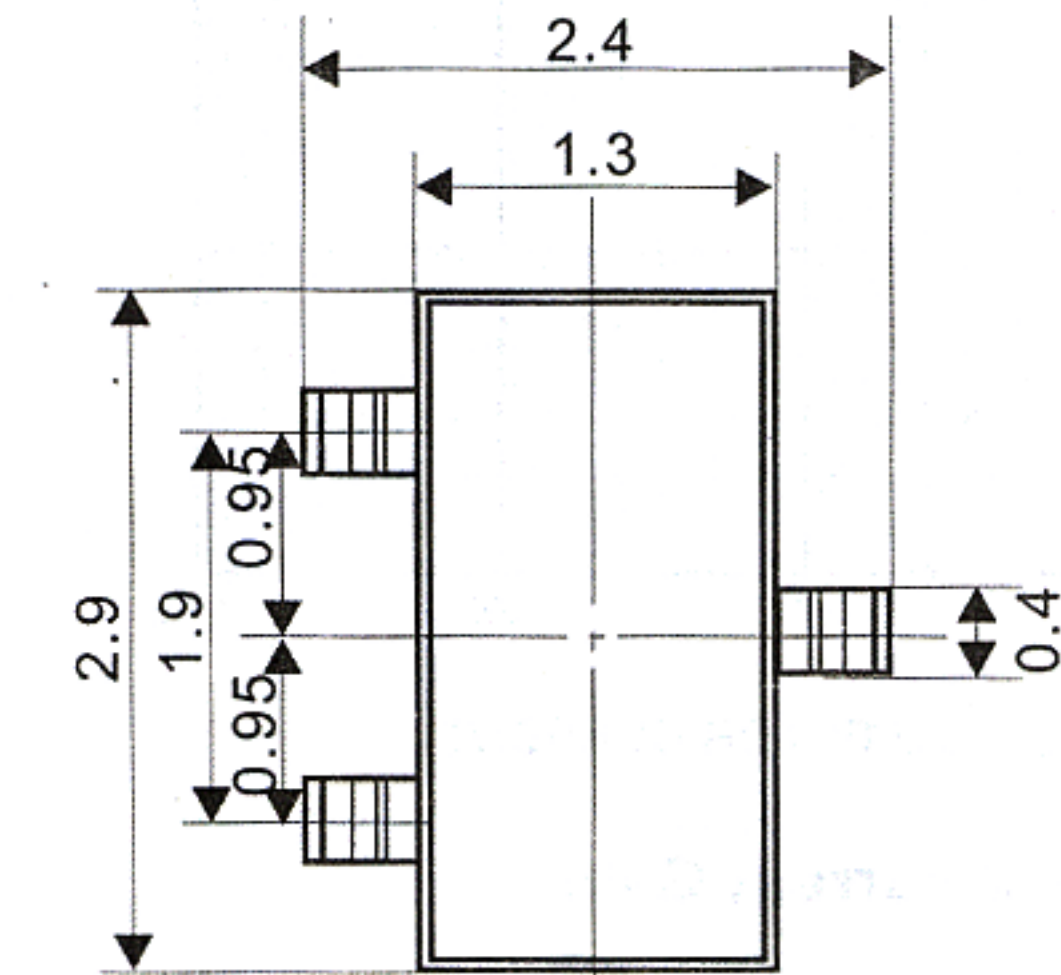
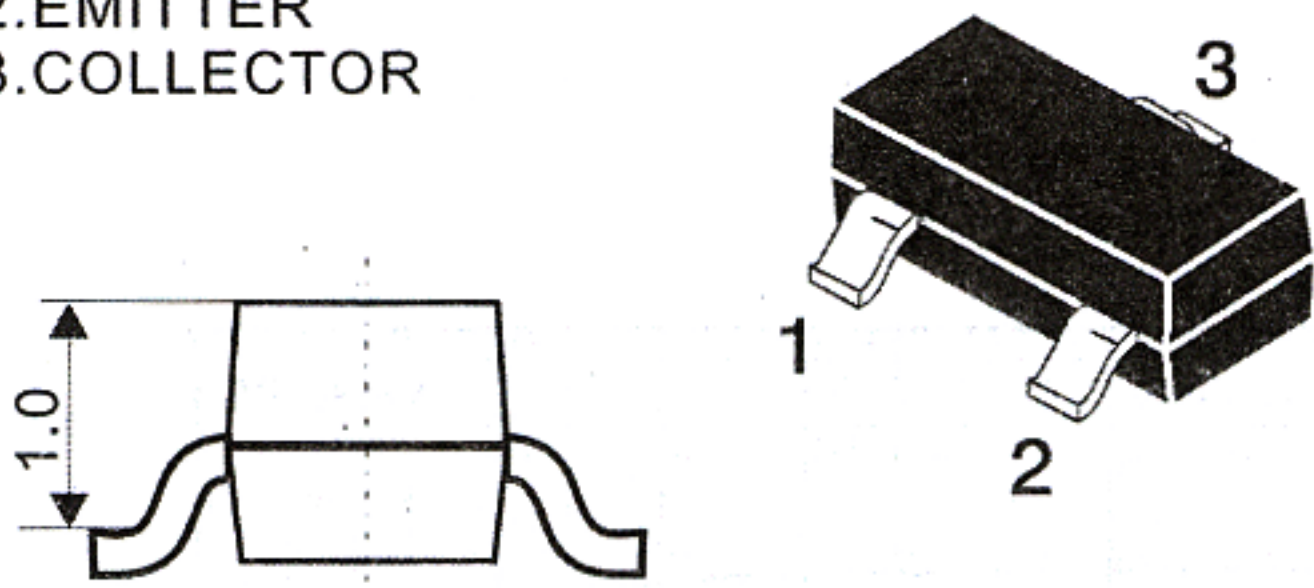


# SOT-23 Plastic-Encapsulate Transistors

## SS8550LT1 TRANSISTOR (PNP)

- 1.BASE
- 2.EMITTER
- 3.COLLECTOR



UNIT: mm

### FEATURES

#### Power dissipation

$P_{CM}$ : 0.625 W ( $T_{amb}=25^{\circ}C$ )

#### Collector current

$I_{CM}$ : -1.5 A

#### Collector-base voltage

$V_{(BR)CBO}$ : -40V

#### Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

### ELECTRICAL CHARACTERISTICS

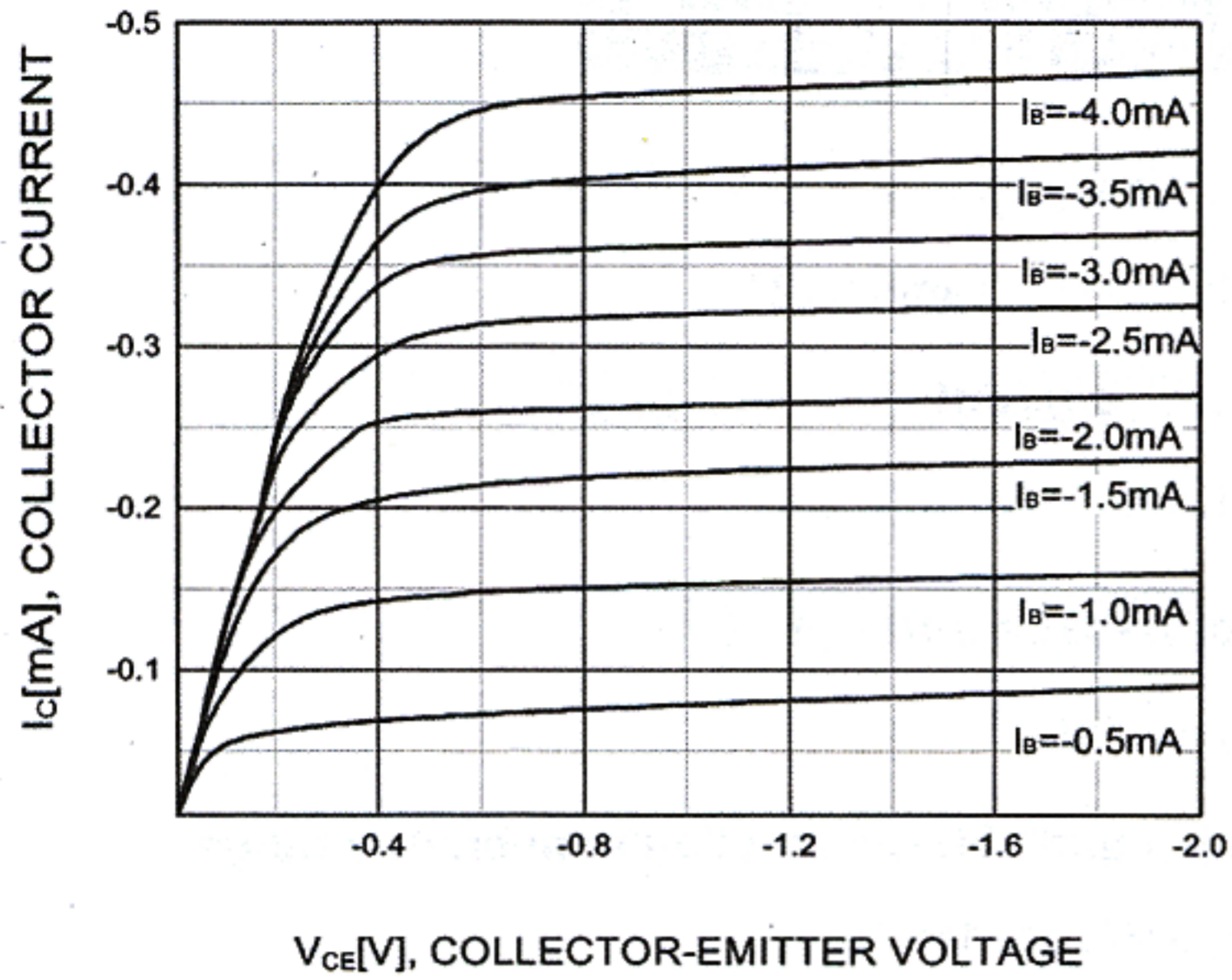
( $T_{amp}=25^{\circ}C$  unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-0.1mA, I_B=0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-40V, I_E=0$			-0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE}=-20V, I_B=0$			-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5V, I_C=0mA$			-0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-100mA$	120		350	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-800mA$	40			
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C=-800mA, I_B=-80mA$			-0.5	V
Base-emitter saturation voltage	$V_{BEsat}$	$I_C=-800mA, I_B=-80mA$			-1.2	V
Base-emitter voltage	$V_{BEF}$	$I_E=-1.5A$			-1.6	V
Transition frequency	$f_T$	$V_{CE}=-10V, I_C=-50mA, f=30MHz$	100			MHz

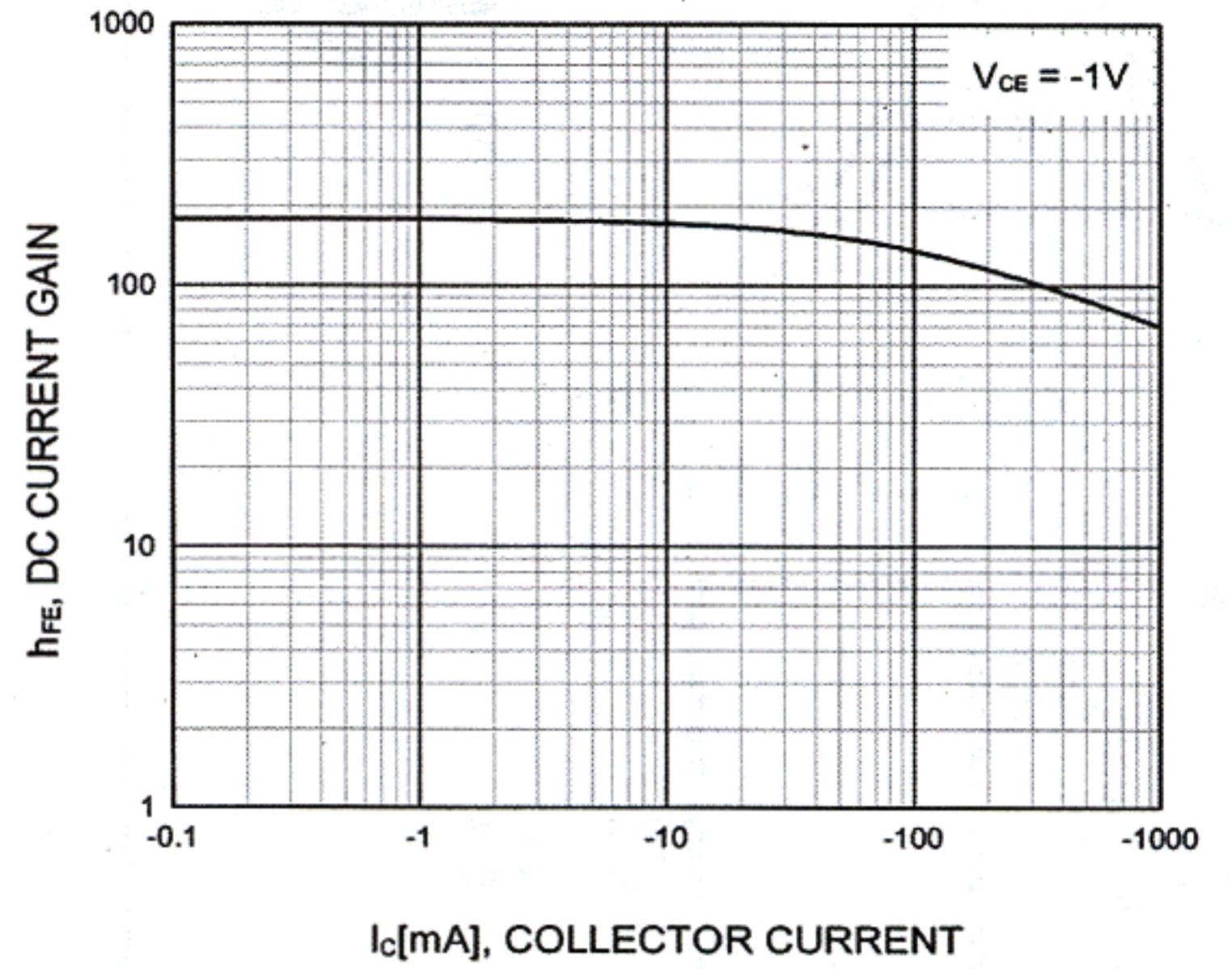
### CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H
Range	120-200	200-350

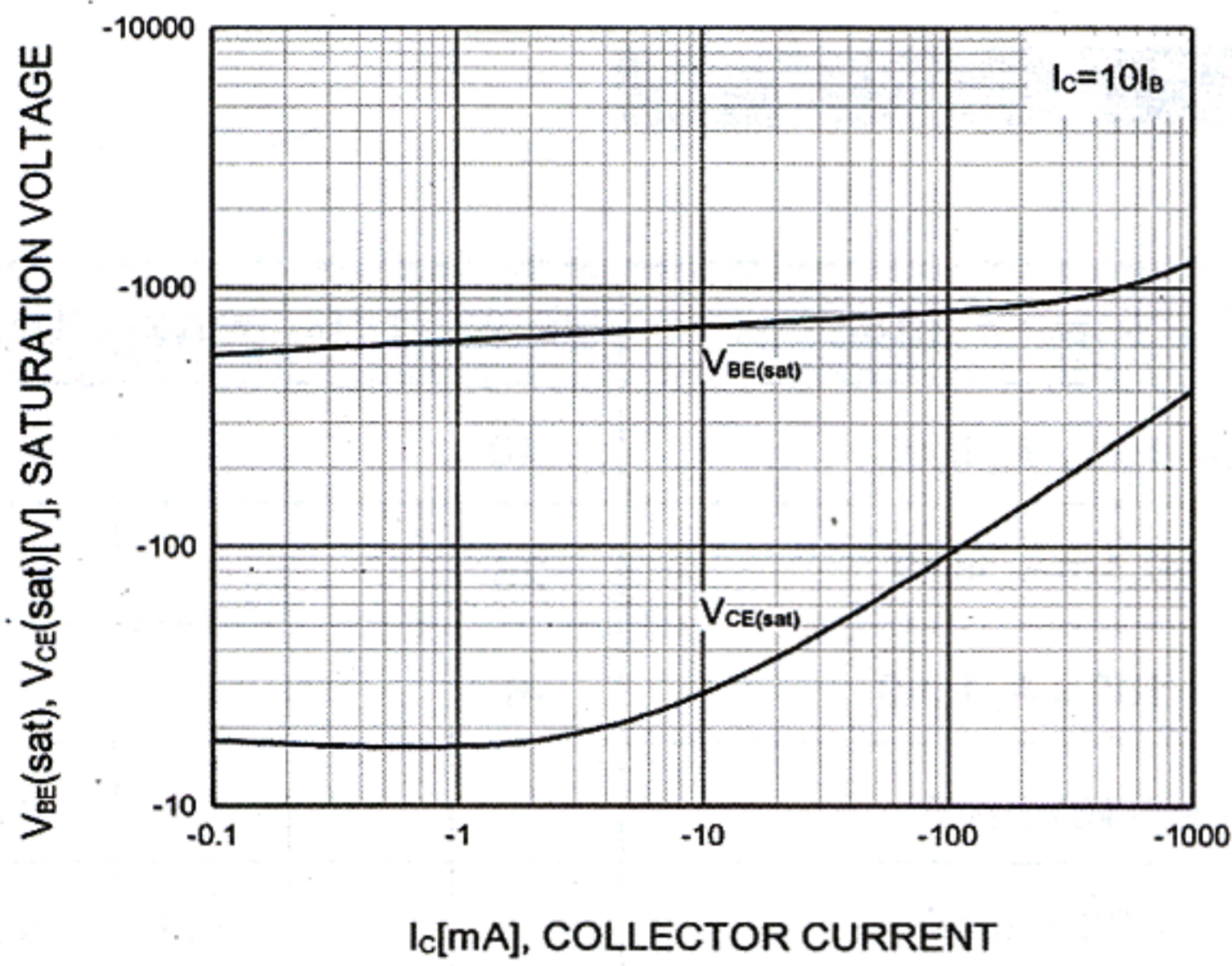
DEVICE MARKING : SS8550LT1=Y2



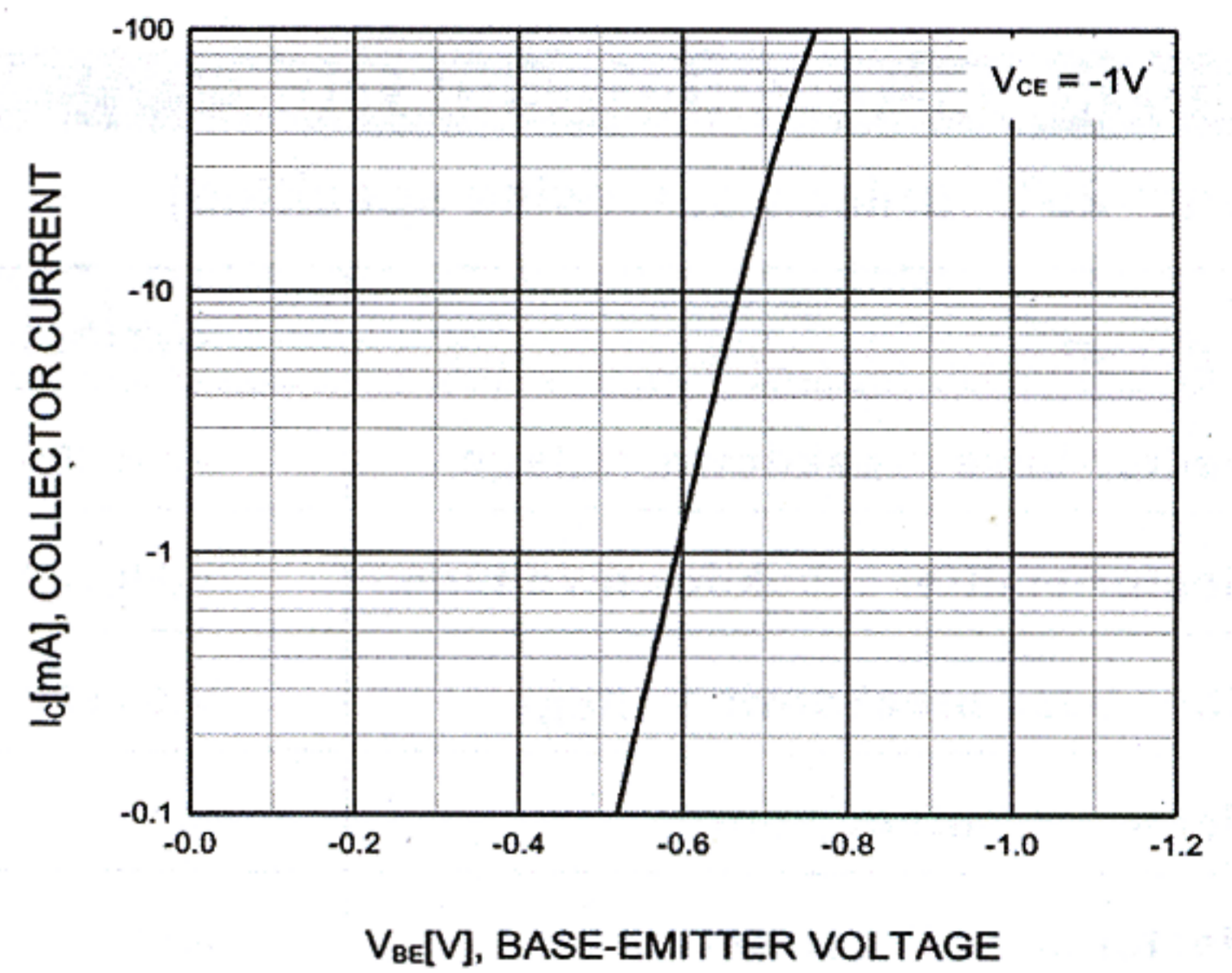
Static Characteristic



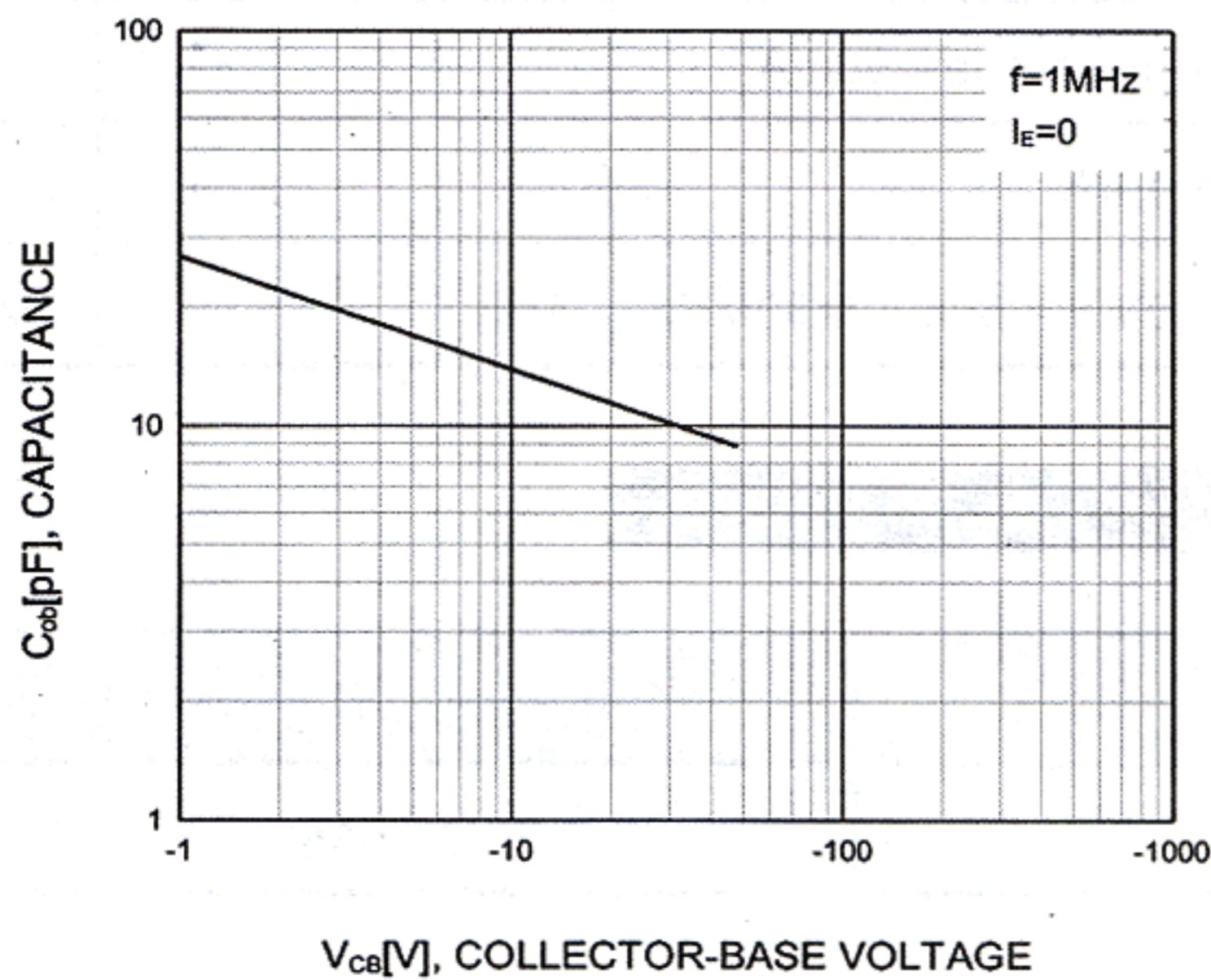
DC current Gain



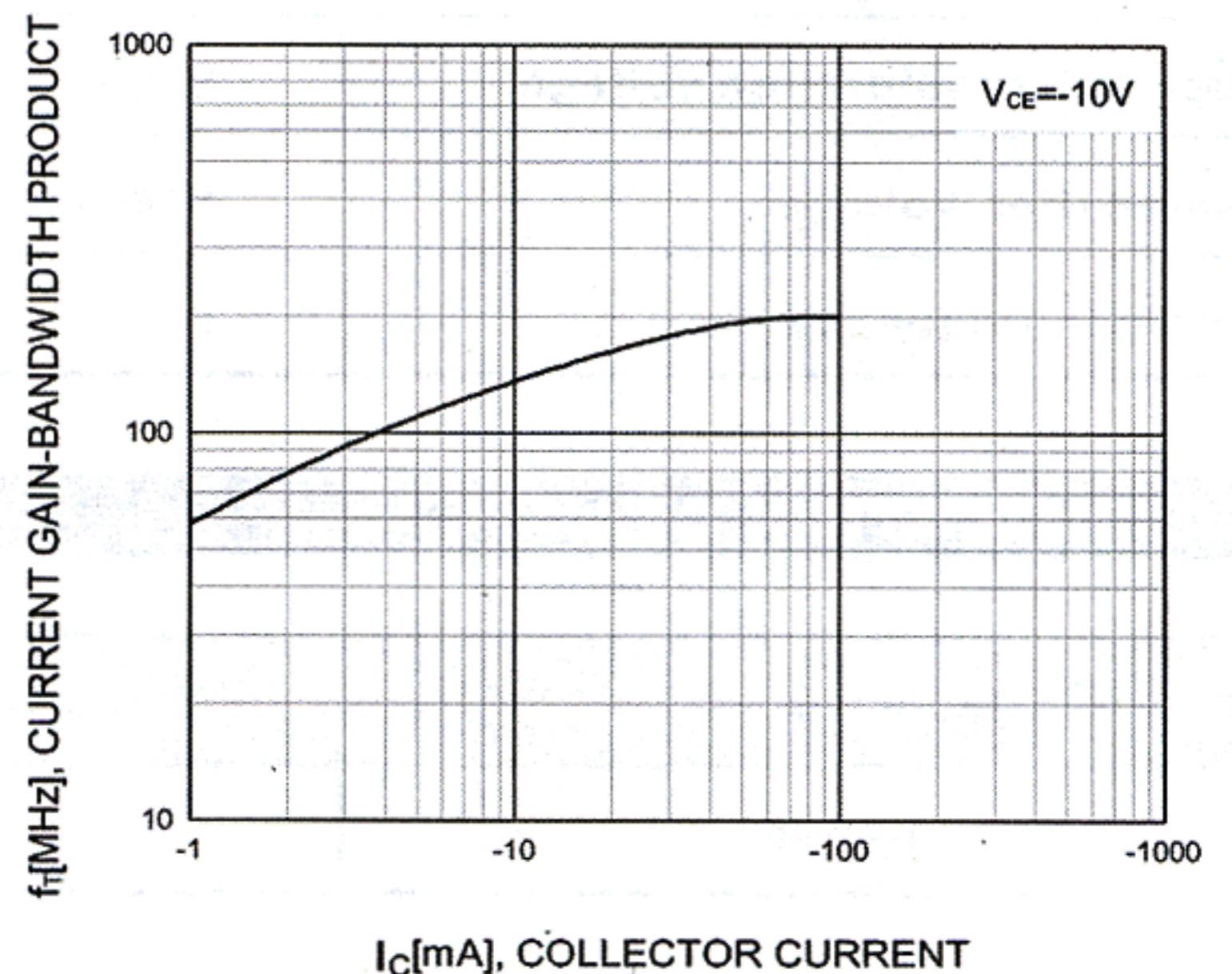
Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage



Base-Emitter On Voltage



Collector Output Capacitance



Current Gain Bandwidth Product